

Notice of References Cited	Application/Control No. 10/558,271		Applicant(s)/Patent Under Reexamination TATSUMI ET AL.	
	Examiner JAMI M. VALENTINE		Art Unit 2815	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2003/0045080 A1	03-2003	Visokay et al.	438/591
*	B	US-2003/0218223 A1	11-2003	Nishiyama et al.	257/410
*	C	US-6,780,708 B1	08-2004	Kinoshita et al.	438/241
	D	US-			
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	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)			
	U	Wilk et al., "Electrical properties of hafnium silicate gate dielectrics deposited directly on silicon" Applied Physics Letters 74, 2854 (1999).			
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	X				

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.